

N-channel 30 V 6 mΩ logic level MOSFET in LFPAK Rev. 04 — 10 March 2011 Produc

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. **Quick reference data**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|------|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 30 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u> | - | - | 79 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 55 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static cha | racteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C | - | 4.26 | 6 | mΩ |
| Dynamic o | haracteristics | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ | - | 3.08 | - | nC |
| Q _{G(tot)} | total gate charge | V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u> | - | 11 | - | nC |
| Avalanche | e ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | | - | - | 26 | mJ |
| | | | | | | |

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2. Pinning information

| Table 2. | Pinning | j information | | |
|----------|---------|-----------------------------------|---|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S | source | | _ |
| 2 | S | source | mb | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | mbb076 S |
| | | | SOT669 (LFPAK) | |

3. Ordering information

| Table 3. Ordering i | nformation | | |
|---------------------|------------|---|---------|
| Type number | Package | | |
| | Name | Description | Version |
| PSMN6R0-30YL | LFPAK | plastic single-ended surface-mounted package (LFPAK); 4 leads | SOT669 |

4. Limiting values

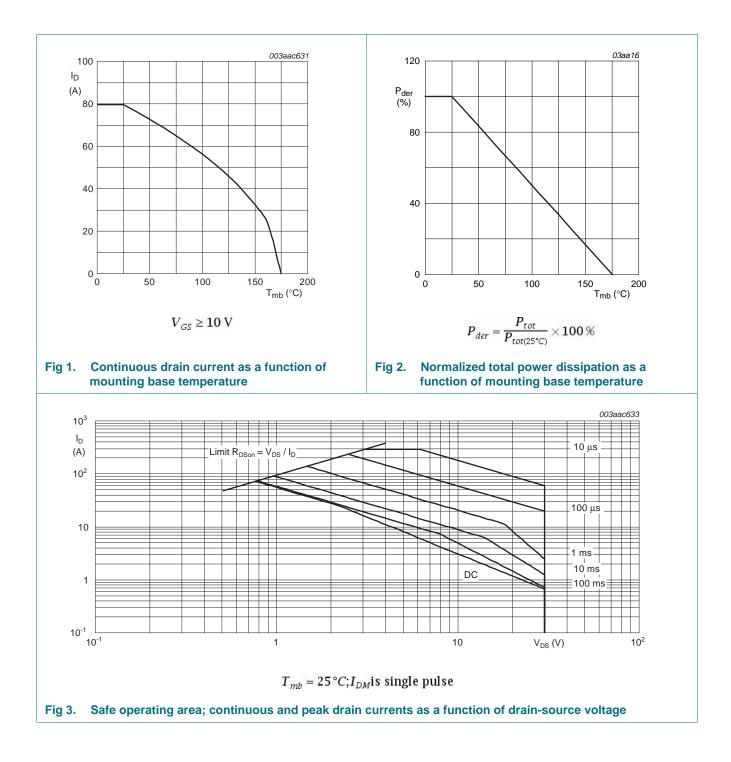
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|--|---|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 30 | V |
| V _{DSM} | peak drain-source voltage | $t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 110 \text{ nJ};$ pulsed | - | 35 | V |
| V _{DGR} | drain-gate voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 30 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u> | - | 56 | А |
| | | V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> | - | 79 | А |
| I _{DM} | peak drain current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u> | - | 292 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 55 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| Source-drai | n diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 73 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 292 | А |
| Avalanche r | uggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 73 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω ; unclamped | - | 26 | mJ |
| | | | | | |

PSMN6R0-30YL

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5. Thermal characteristics

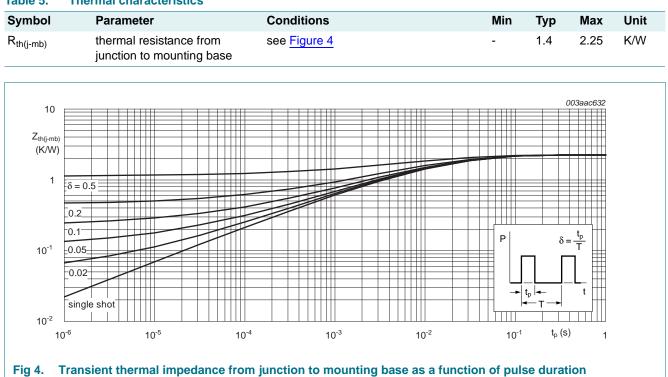


Table 5. Thermal characteristics

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6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------------|--------------------------------------|---|------|------|------|------|
| Static chara | cteristics | | | | | |
| V _{(BR)DSS} drain-source | | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C | 27 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12 | 1.3 | 1.7 | 2.15 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 12</u> | 0.65 | - | - | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 12</u> | - | - | 2.45 | V |
| DSS | drain leakage current | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 1 | μA |
| | | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | 100 | μA |
| GSS | gate leakage current | V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C | - | 6.18 | 7.87 | mΩ |
| resis | resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 150 °C; see <u>Figure 13</u> | - | - | 10.5 | mΩ |
| | | V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C | - | 4.26 | 6 | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 0.63 | 1.5 | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} total gate charge | total gate charge | $I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u> | - | 11 | - | nC |
| | | $I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u> | - | 24 | - | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 22 | - | nC |
| Q _{GS} | gate-source charge | $I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ | - | 4.2 | - | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | see <u>Figure 14;</u> see <u>Figure 15</u> | - | 2.4 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 1.8 | - | nC |
| Q _{GD} | gate-drain charge | | - | 3.08 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | V _{DS} = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u> | - | 2.6 | - | V |
| C _{iss} | input capacitance | $V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ | - | 1425 | - | pF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } Figure 16$ | - | 313 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 155 | - | pF |
| d(on) | turn-on delay time | V_{DS} = 12 V; R _L = 0.5 Ω; V _{GS} = 4.5 V; | - | 25 | - | ns |
| r | rise time | $R_{G(ext)} = 4.7 \Omega$ | - | 43 | - | ns |
| d(off) | turn-off delay time | | - | 31 | - | ns |
| t _f | fall time | | - | 11 | - | ns |
| | | | | | | |

Symbol

V_{SD}

Source-drain diode

PSMN6R0-30YL

Typ

0.88

Max

1.2

Unit

V

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Min

$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ t_{rr} reverse recovery time 32 -ns $V_{DS} = 20 V$ recovered charge 25 nC Qr --003aac625 003aac627 100 80 10 I_D I_D (A) 4.5 (A) 80 60 60 40 $V_{GS}(V) = 3.2$ 40 3. 20 20 T_i = 150 °C 2.8 25 °C 2.6-24 0 0 2 4 6 8 _{VDS} (V)¹⁰ 0 1 2 3 V_{GS} (V) 4 0 $T_{i} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ $V_{DS} = 10V$ Transfer characteristics: drain current as a Fig 5. Output characteristics: drain current as a Fig 6. function of drain-source voltage; typical values function of gate-source voltage; typical values 003aac630 003aac636 20 2500 С R_{DSor} Cicc (pF) (mΩ) 2000 15 $V_{GS}(V) = 3.2$ Crss 1500 10 4.5 1000 10 5 500 0 0 0 10 20 30 0 2 4 6 8 _{VGS} (V) 10 I_D (A) 40 $T_j = 25 \,^{\circ}C$ $V_{DS} = 0V; f = 1MHz$ Drain-source on-state resistance as a function Fig 8. Input and reverse transfer capacitances as a Fig 7. of drain current; typical values function of gate-source voltage; typical values

Table 6. Characteristics ...continued

Parameter

Tested to JEDEC standards where applicable.

source-drain voltage

Conditions

see Figure 17

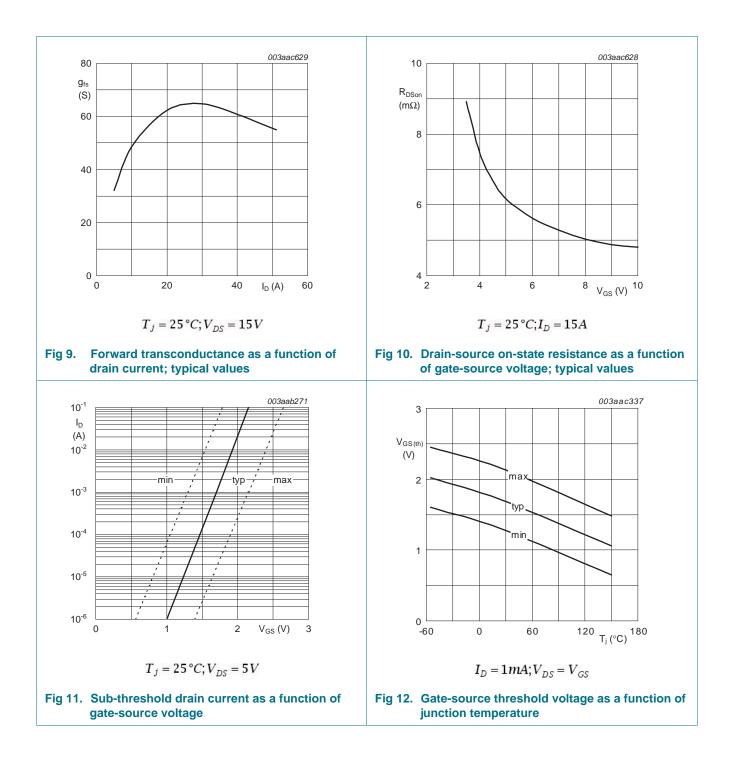
I_S = 25 A; V_{GS} = 0 V; T_i = 25 °C;

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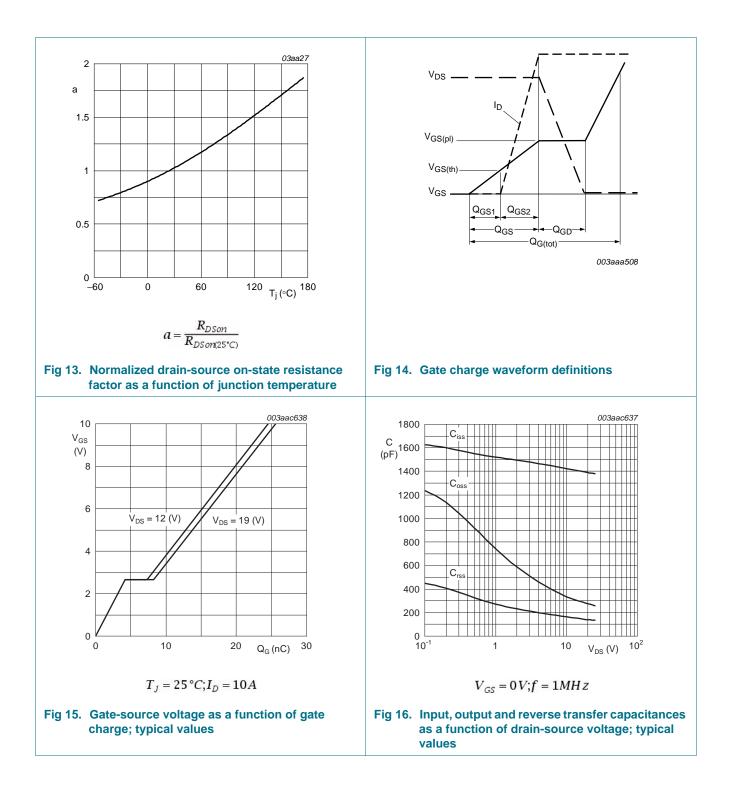
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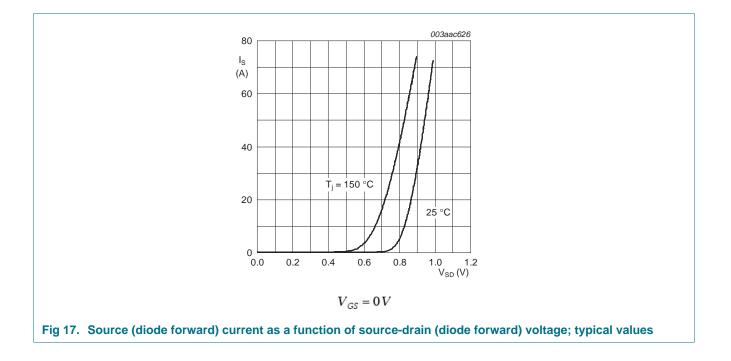
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N-channel 30 V 6 m Ω logic level MOSFET in LFPAK

7. Package outline

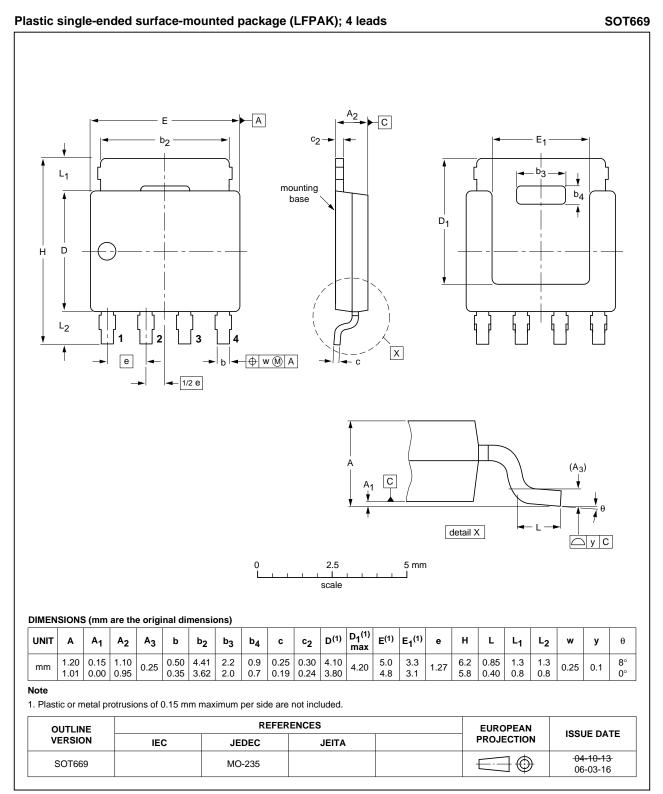


Fig 18. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7.Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|---------------------------------------|--------------------|---------------|------------------|
| PSMN6R0-30YL v.4 | 20110310 | Product data sheet | - | PSMN6R0-30YL v.3 |
| Modifications: | Various changes f | to content. | | |
| PSMN6R0-30YL v.3 | 20100104 | Product data sheet | - | PSMN6R0-30YL v.2 |

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| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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